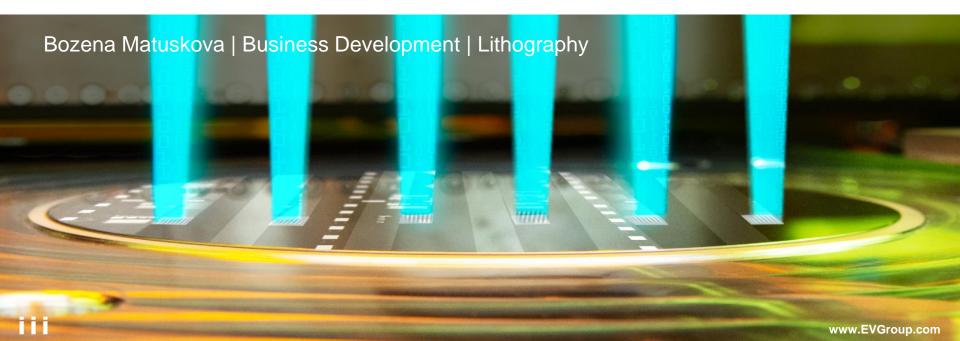


LITHOSCALE®

A milestone towards digital lithography in high volume manufacturing



EV Group | At A Glance



Leading supplier of wafer processing equipment for the MEMS, nanotechnology and semiconductor markets

Founded in 1980 by DI Erich and Aya Maria Thallner. More than 1000 employees worldwide

Headquarters in Austria, with fully owned subsidiaries in the USA, Japan, South Korea, China and Taiwan

Recent Developments



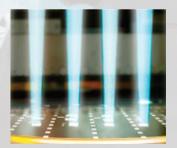
GEMINI® FB Hybrid Bonding



EVG®850 DB Laser Debonding



BONDSCALE™ Fusion Bonding



EVG[®] MLE™ Maskless Exposure Technology



EVG® HERCULES® NIL SmartNIL® UV-NIL Up to 300 mm

Motivation | Future Challenges for Backend Lithography



→ Flexibility

- Fast innovation and design tape out for improved time to market
- Short development cycles and immediate ramp up from R&D to HVM
- High product mix demands mix and match with minimal retooling time
- Flexible dynamic patterning solution with high depth of focus and high resolution
- Confidentiality of new designs

Scalability

- Patterning of various substrate sizes and materials such as mold, silicon or laminates
- Adaptability to high substrate stress, bow and warp

Cost of ownership

- High throughput with low resolution
- Low consumable cost
- High mask cost for different chip designs and mask inventory management

MLE™ Maskless Exposure Technology | Transforming Idea to Reality





- Real-time layout processing & patterning
- Exposure of individual stripes
- Fine sub-grid address for smooth edges
- Scalability by adding/ removing exposure heads in substrate sizes from wafers to panels



Advanced Alignment Capabilities

- VIS top-side alignment & backside alignment for enhanced compensation features
- Individual alignment capabilities throughout the wafer surface



Mask-less flexibility & agility

- High product-mix variation improving CoO values
- Agile smart processing & design mix
- Consumables-free technology



Parameter	Specification
Exposure Source	HP UV - Laser Diode (LD)
Exposure Spectrum [nm] (single or mixed)	375 nm 405 nm
DoF [µm]	24 µm
Substrate Sizes [round/square]	up to 12"
Wafer layouts [formats]	GDS II (standard) Gerber, OASIS, ODB++ (optional)

General Business

MLE™ | Highlights & Unique Values



Compensates

- Mechanical die placement and stress induced inaccuracies via adaptive registration
- High order substrate deformations, e.g. thick wafers glasses and organic substrates

Enables

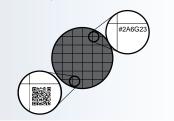
- Individual die layouts (serial numbers, encryption keys)
- Die & wafer level design patterns
- Mix & match with minimal switch-over
- Seamless stitching
- Contactless WEC and surface scan

Delivers

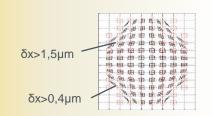
- In-line capability, long lifetime, cost-efficient light sources
- Mask-less flexibility
- Large, small, non-standard, multiple wafers or rectangular substrates (panels) for a multitude of processes

High-order, placement, scaling error corrections expansion distortion

Die-level annotation, serial numbers



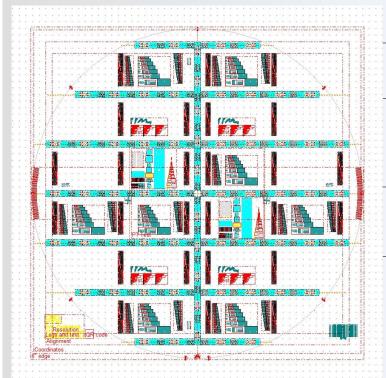
Bow substrates, surface in-variations



LITHOSCALE® | Wavelength vs Dosis vs Focus Exposure Matrix



- Numerous process conditions tested at once & in real environment
- User defined & can vary for each material
 - dose steps vs wavelengths
 - Dose range variation:
 - 50mJ 4000mJ
 - **Exposure wavelength** range variation:
 - 375 nm
 - 405 nm
 - 375 + 405nm (broadband: 100% / 100%)
 - or any kind of mixture (20% / 80%, ..)
 - dose steps vs focus position steps
 - Dose range variation:
 - depends on first matrix result
 - Focus position range variation:
 - -12 .. 12µm

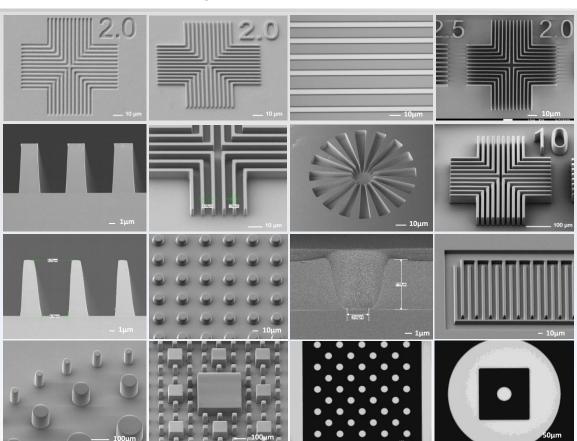


EVG test layout example

- → Alignment pattern
- → Test structures: round, square vias
- → Standard L/S variation test pattern
- → Various additional test patterns: siemens star. taper

LITHOSCALE® | Applications & Process Results





Thin Resists

- → Fine-line RDL structuring, Lift-off applications
 - Pos. AZ MIR 701, LT: 1μm
 - Neg. AZ nLOF, LT: 2μm
 - Pos. AZ 12XT, LT: 10μm
 - Pos. Sumitomo, AR 3.5:1, 7:1

Thick Resists

- → Bumping, core-line RDL structuring, high AR
 - Pos. TOK P-W1000T, LT 8μm, AR: 4:1 sidewall angle: 87°
 - Neg. JSR THB 151N, LT 50µm, AR 5:1

Dielectrics

- → Buffer layer for stress & thermal optimisation
 - Pos. JSR WPR5100, LT 7μm, AR 2:1 sidewall angle: 82°
 - Neg. FUJIFILM LTC Series, LT 7µm, AR: 2:1

ORDL, Photonics, MEMS Applications

- → Photonics packaging, MEMS, coloured resists
 - Neg. SU-8 GM1075, LT 100 600μm
 - Neg. Black resist (FFEM), LT 1 6μm

General Business

LITHOSCALE® | Executive Summary





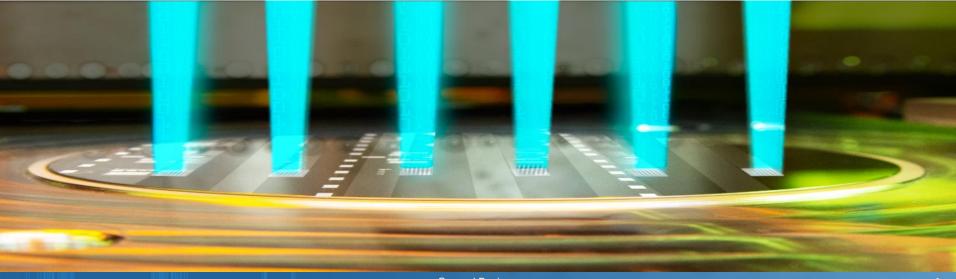
- High product variation
- Agile processing & design mix
- Digital infrastructure
- Low cost multi design logistics
- Consumables-free technology

Individual Die Processing

- Exposure of individual stripes
- Small raster size for smooth edges
- Grayscale intensity modulation
- Dynamic die annotation

Fast Full-Field Positioning

- VIS, top-side alignment, nIR backside alignment for interposer, advanced packaging and MEMS processing
- Scalability in substrate sizes from wafers to panels



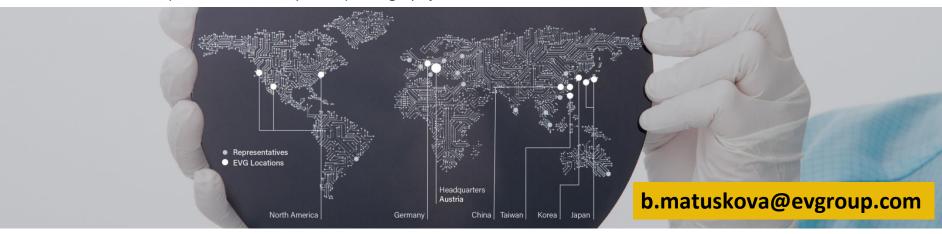


General Business



Thank you for your attention.

Bozena Matuskova | Business Development | Lithography



EPIC Members New Product Release, 14.10.2020

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